

# MJE5740G, MJE5742G

## NPN Silicon Power Darlington Transistors

The MJE5740G and MJE5742G Darlington transistors are designed for high-voltage power switching in inductive circuits.

### Features

These Devices are Pb-Free and are RoHS Compliant\*

### Applications

- Small Engine Ignition
- Switching Regulators
- Inverters
- Solenoid and Relay Drivers
- Motor Controls

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJE5740 MJE5742	$V_{CEO(sus)}$	300 400	Vdc
Collector-Emitter Voltage MJE5740 MJE5742	$V_{CEV}$	600 800	Vdc
Emitter-Base Voltage	$V_{EB}$	8	Vdc
Collector Current - Continuous - Peak (Note 1)	$I_C$ $I_{CM}$	8 16	Adc
Base Current - Continuous - Peak (Note 1)	$I_B$ $I_{BM}$	2.5 5	Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25 C	$P_D$	2 0.016	W W/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25 C	$P_D$	100 0.8	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	$T_L$	275	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq 10\%$ .

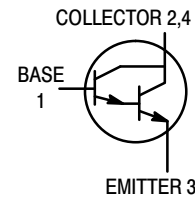
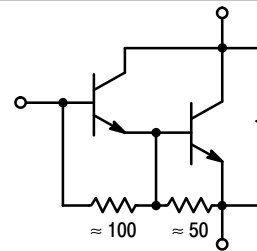
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



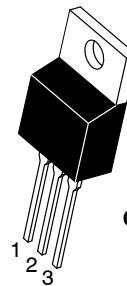
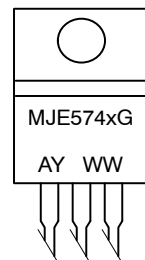
ON Semiconductor®

<http://onsemi.com>

## POWER DARLINGTON TRANSISTORS 8 AMPERES 300-400 VOLTS 80 WATTS



### MARKING DIAGRAM



TO-220AB  
CASE 221A-09  
STYLE 1

MJE574x = Device Code  
x = 0 or 2  
G = Pb-Free Package  
A = Assembly Location  
Y = Year  
WW = Work Week

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# MJE5740G, MJE5742G

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b> (Note 2)					
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0)	MJE5740 MJE5742 V <sub>CEO(sus)</sub>	300 400	– –	– –	Vdc
Collector Cutoff Current (V <sub>CEV</sub> = Rated Value, V <sub>BE(off)</sub> = 1.5 Vdc) (V <sub>CEV</sub> = Rated Value, V <sub>BE(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 100°C)	I <sub>CEV</sub>	– –	– –	1 5	mAdc
Emitter Cutoff Current (V <sub>EB</sub> = 8 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	–	75	mAdc

## SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased	I <sub>S/b</sub>	See Figure 6			
Clamped Inductive SOA with Base Reverse Biased	RBSOA	See Figure 7			

## ON CHARACTERISTICS

 (Note 2)

DC Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 5 Vdc)	h <sub>FE</sub>	50 200	100 400	– –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 4 Adc, I <sub>B</sub> = 0.2 Adc) (I <sub>C</sub> = 8 Adc, I <sub>B</sub> = 0.4 Adc) (I <sub>C</sub> = 4 Adc, I <sub>B</sub> = 0.2 Adc, T <sub>C</sub> = 100°C)	V <sub>CE(sat)</sub>	– – –	– – –	2 3 2.2	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = 4 Adc, I <sub>B</sub> = 0.2 Adc) (I <sub>C</sub> = 8 Adc, I <sub>B</sub> = 0.4 Adc) (I <sub>C</sub> = 4 Adc, I <sub>B</sub> = 0.2 Adc, T <sub>C</sub> = 100°C)	V <sub>BE(sat)</sub>	– – –	– – –	2.5 3.5 2.4	Vdc
Diode Forward Voltage (Note 3) (I <sub>F</sub> = 5 Adc)	V <sub>f</sub>	–	–	2.5	Vdc

## SWITCHING CHARACTERISTICS

Typical Resistive Load (Table 1)						
Delay Time	(V <sub>CC</sub> = 250 Vdc, I <sub>C(pk)</sub> = 6 A I <sub>B1</sub> = I <sub>B2</sub> = 0.25 A, t <sub>p</sub> = 25 μs, Duty Cycle ≤ 1%)	t <sub>d</sub>	–	0.04	–	μs
Rise Time		t <sub>r</sub>	–	0.5	–	μs
Storage Time		t <sub>s</sub>	–	8	–	μs
Fall Time		t <sub>f</sub>	–	2	–	μs
Inductive Load, Clamped (Table 1)						
Voltage Storage Time	(I <sub>C(pk)</sub> = 6 A, V <sub>CE(pk)</sub> = 250 Vdc I <sub>B1</sub> = 0.06 A, V <sub>BE(off)</sub> = 5 Vdc)	t <sub>sv</sub>	–	4	–	μs
Crossover Time		t <sub>c</sub>	–	2	–	μs

2. Pulse Test: Pulse Width 300 μs, Duty Cycle = 2%.

3. The internal Collector–to–Emitter diode can eliminate the need for an external diode to clamp inductive loads. Tests have shown that the Forward Recovery Voltage (V<sub>f</sub>) of this diode is comparable to that of typical fast recovery rectifiers.

## ORDERING INFORMATION

Device	Package	Shipping
MJE5740G	TO–220 (Pb–Free)	50 Units / Rail
MJE5742G	TO–220 (Pb–Free)	

TYPICAL CHARACTERISTICS

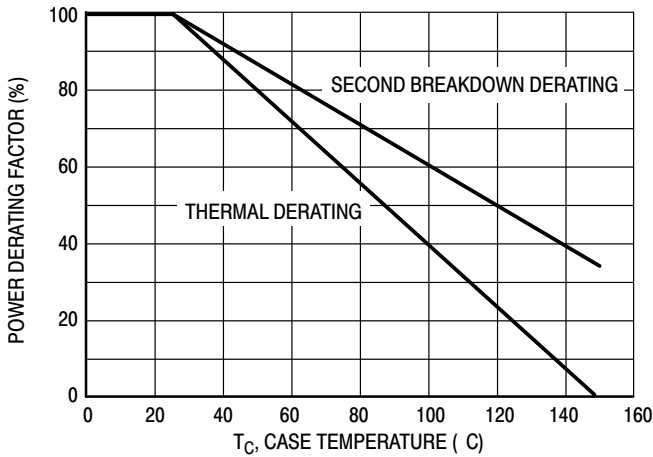


Figure 1. Power Derating

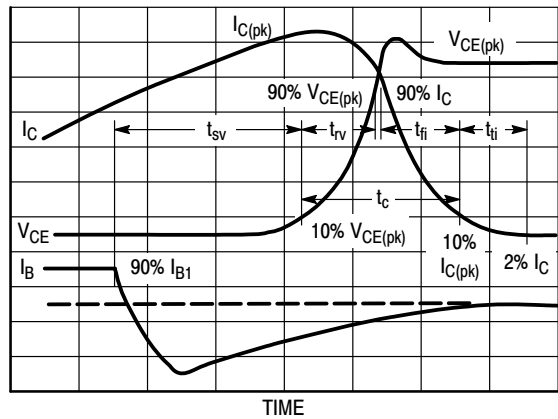


Figure 2. Inductive Switching Measurements

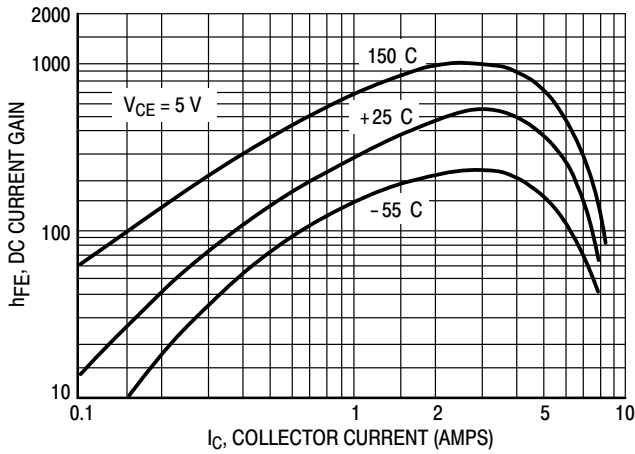


Figure 3. DC Current Gain

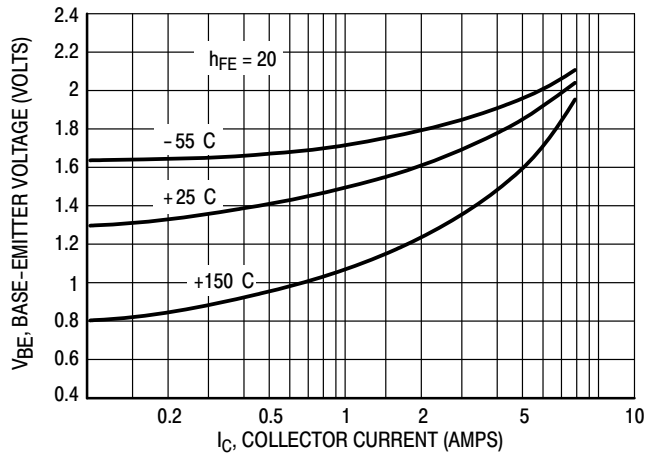


Figure 4. Base-Emitter Voltage

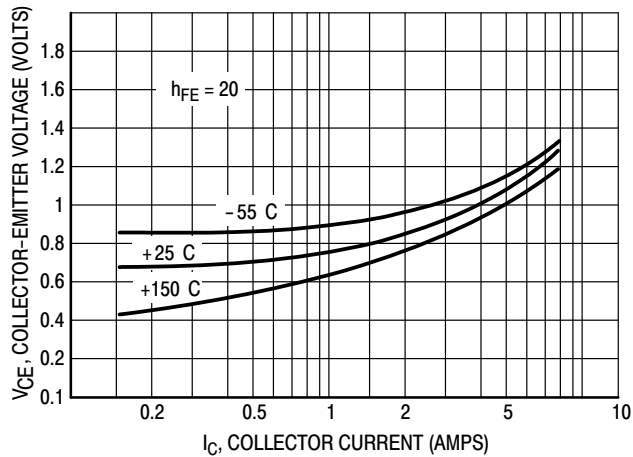


Figure 5. Collector-Emitter Saturation Voltage

# MJE5740G, MJE5742G

Table 1. Test Conditions for Dynamic Performance

REVERSE BIAS SAFE OPERATING AREA AND INDUCTIVE SWITCHING		RESISTIVE SWITCHING
TEST CIRCUITS	<p>DUTY CYCLE <math>\leq 10\%</math>  <math>t_r, t_f \leq 10 \text{ ns}</math></p> <p>NOTE:  PW and <math>V_{CC}</math> Adjusted for Desired <math>I_C</math>  <math>R_B</math> Adjusted for Desired <math>I_{B1}</math></p>	<p>*SELECTED FOR <math>\geq 1 \text{ kV}</math></p>
CIRCUIT VALUES	<p>COIL DATA:  FERROXCUBE CORE #6656  FULL BOBBIN (~16 TURNS) #16</p> <p>GAP FOR 200 <math>\mu\text{H}/20 \text{ A}</math>  <math>L_{\text{coil}} = 200 \mu\text{H}</math></p> <p><math>V_{CC} = 30 \text{ V}</math>  <math>V_{CE(\text{pk})} = 250 \text{ Vdc}</math>  <math>I_{C(\text{pk})} = 6 \text{ A}</math></p>	<p><math>V_{CC} = 250 \text{ V}</math>  <math>D1 = 1\text{N}5820 \text{ OR EQUIV.}</math></p>
TEST WAVEFORMS	<p><b>OUTPUT WAVEFORMS</b></p> <p><math>t_1</math> ADJUSTED TO OBTAIN <math>I_C</math></p> $t_1 \approx \frac{L_{\text{coil}} (I_{C(\text{pk})})}{V_{CC}}$ <p>TEST EQUIPMENT  SCOPE-TEKTRONICS  475 OR EQUIVALENT</p> $t_2 \approx \frac{L_{\text{coil}} (I_{C(\text{pk})})}{V_{\text{clamp}}}$	<p><math>t_r, t_f &lt; 10 \text{ ns}</math>  DUTY CYCLE = 1%  <math>R_B</math> AND <math>R_C</math> ADJUSTED  FOR DESIRED <math>I_B</math> AND <math>I_C</math></p>

SAFE OPERATING AREA INFORMATION

FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_C = 25^\circ\text{C}$ ;  $T_{J(pk)}$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when  $T_C \geq 25^\circ\text{C}$ . Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 6 may be found at any case temperature by using the appropriate curve on Figure 1.

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current condition allowable during reverse biased turnoff. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figure 7 gives the complete RBSOA characteristics.

The Safe Operating Area figures shown in Figures 6 and 7 are specified ratings for these devices under the test conditions shown.

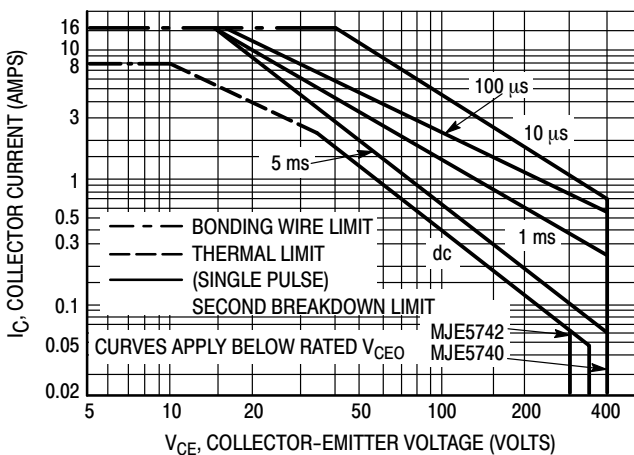


Figure 6. Forward Bias Safe Operating Area

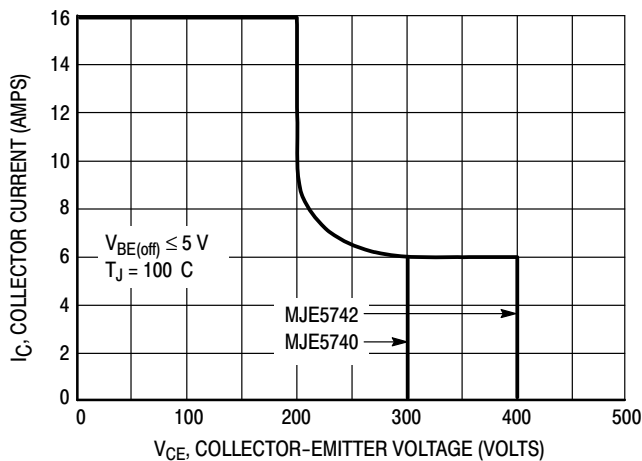


Figure 7. Reverse Bias Safe Operating Area

RESISTIVE SWITCHING PERFORMANCE

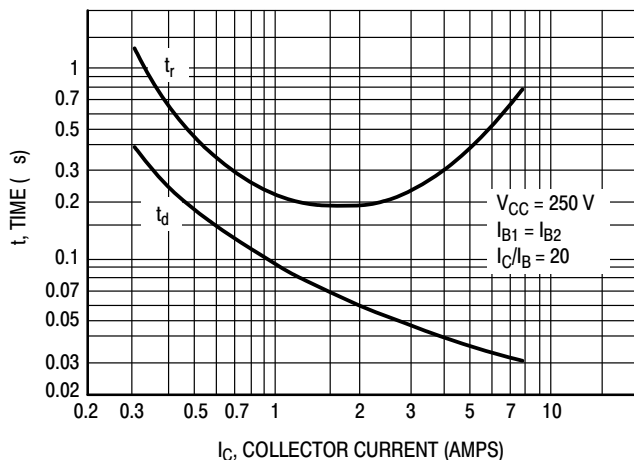


Figure 8. Turn-On Time

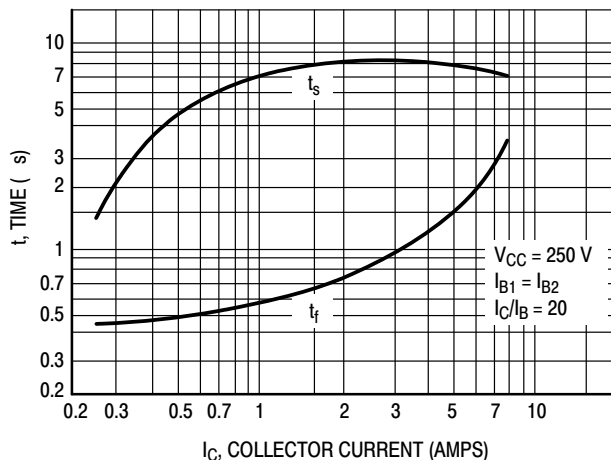
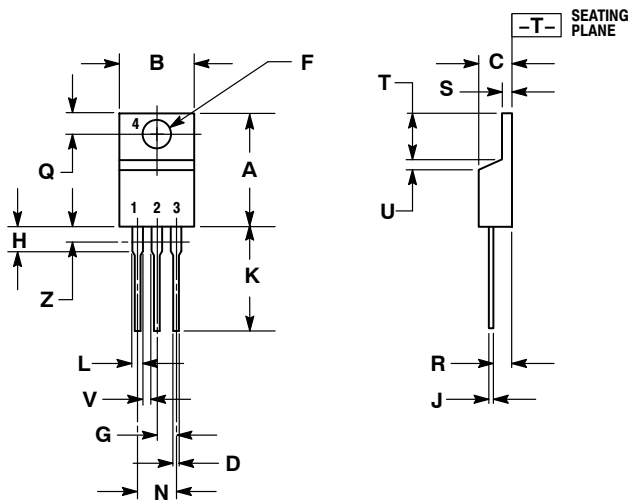


Figure 9. Turn-Off Time

# MJE5740G, MJE5742G

## PACKAGE DIMENSIONS

### TO-220 CASE 221A-09 ISSUE AG



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

#### STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free  
USA/Canada

Europe, Middle East and Africa Technical Support:  
Phone: 421 33 790 2910

Japan Customer Focus Center  
Phone: 81-3-5817-1050

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative